14. An EL device of claim 1, wherein the wide energy gap semiconductor layer having *n*-type conductivity over the said CNC layer is replaced by a dielectric layer.

15. An electroluminescent device of claim 13, wherein the dielectric layers are selected from the group consisting of SiON, Ta_2O_5, $Ba_xSr_{1-x}TiO_3$, PLZT, $Zn_xMg_{1-x}S$, $Zn_xBe_{1-x}S$, etc., or their combination.

16. An electroluminescent device of claim 14, wherein dielectric layers are selected from the group consisting of SiON, Ta_2O_5, $Ba_xSr_{1-x}TiO_3$, PLZT, $Zn_xMg_{1-x}S$, $Zn_xBe_{1-x}S$, etc., or their combinations.--

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Please cancel claim 17.

Please rewrite claim 18 as follows:

--18. An device of claim 1, wherein the wide energy gap semiconductor layer having n-type conductivity over said CNC layer is replaced by a hole-blocking layer.--

Please cancel claim19.

Please cancel claim 21.

Please rewrite claim 22 as follows:

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--22. A device of claim 1, wherein the *p*-doped wide energy gap semiconductor layer underneath the said CNC layer is replaced by a hole-transporting organic semiconductor layer. --

Please cancel claims 23-24.

Please cancel claim 28.

Please cancel claims 30-37.

Please rewrite claims 38-39 as follows:

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--38. An electroluminescent device of claim 22, wherein both hole-transporting layer and CNC layer is substituted by a viscous composite comprising of CNCs, hole-transporting organic semiconductors, oxidative agents, soluble salts and low vapor pressure viscosity-modifying agents.

39. An electroluminescent device of claim 38, wherein viscous composite is contained within appropriate openings realized between said elastomeric spacers.--

Please rewrite claims 41-43 as follows:

A8

--41. An EL device as described in claim 40, wherein the viscous composites are introduced by methods such as screen-printing and ink-jet printing.